

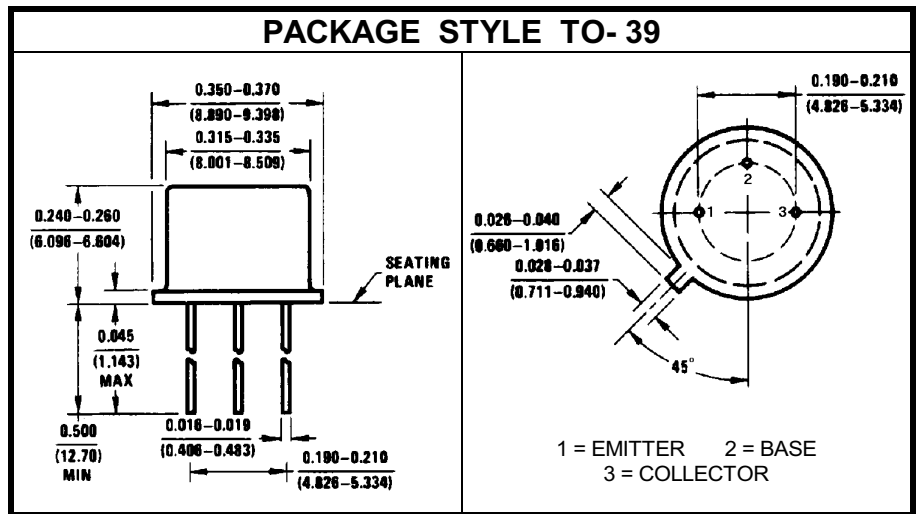
SILICON PNP TRANSISTOR

DESCRIPTION:

The **2N5783** is Designed for General Purpose Amplifier and Switching Applications.

MAXIMUM RATINGS

I_C	3.5 A
I_B	1.0 A
V_{CE}	-40 V
P_{DISS}	10 W @ $T_C = 25^\circ\text{C}$
T_J	-65 $^\circ\text{C}$ to +200 $^\circ\text{C}$
T_{STG}	-65 $^\circ\text{C}$ to +200 $^\circ\text{C}$
θ_{JC}	17.5 $^\circ\text{C}/\text{W}$


CHARACTERISTICS ($T_C=25^\circ\text{C}$)

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 100\text{ mA}$	-40			V
BV_{CER}	$I_C = 100\text{ mA}$ $R_{BE} = 100\ \Omega$	-45			V
BV_{CBO}	$I_C = 100\ \mu\text{A}$	-45			V
I_{CEO}	$V_{CE} = -25\text{ V}$			100	μA
I_{CEX}	$V_{CE} = -45\text{ V}$ $V_{BE} = 1.5\text{ V}$ $T_C = 25^\circ\text{C}$ $V_{CE} = -75\text{ V}$ $V_{BE} = 1.5\text{ V}$ $T_C = 150^\circ\text{C}$			10 1.0	μA mA
I_{EBO}	$V_{EB} = -3.5\text{ V}$			10	μA
h_{FE}	$V_{CE} = -2.0\text{ V}$ $I_C = 1.6\text{ A}$ $I_C = 3.2\text{ A}$	20 4.0		100	---
$V_{CE(SAT)}$	$I_C = 1.6\text{ A}$ $I_B = 0.16\text{ A}$			-1.0	V
$V_{BE(ON)}$	$V_{CE} = 2.0\text{ V}$ $I_C = 1.6\text{ A}$			-1.5	V
$ h_{fe} $	$V_{CE} = -2.0\text{ V}$ $I_C = 100\text{ mA}$ $f = 4.0\text{ MHz}$	2.0		15	---
t_{on}	$V_{CC} = -30\text{ V}$ $I_C = 1.0\text{ A}$ $I_{B1} = I_{B2} = 0.1\text{ A}$			0.5	μS
t_{off}	$V_{CC} = -30\text{ V}$ $I_C = 1.0\text{ A}$ $I_{B1} = I_{B2} = 0.1\text{ A}$			2.5	μS